



RISTON® MM730 & MM740

RISTON® PHOTOPOLYMER FILMS

Performance Data and Processing Information

PRODUCT FEATURES/APPLICATIONS

- Negative working, aqueous processable dry film photo-resist
- Suitable for UV-LASER 355nm direct imaging and conventional exposure
- Vivid print out image after exposure for easy inspection
- Suitable for print and etch, tent and etch with acid or alkaline etching and plate/etch application
- Available in 20, 25, 30 & 38 micron thickness depending on line space required

STORAGE

Temperature: 5-21°C (40-70°F)

Relative Humidity: 30-70%

PRODUCT DESCRIPTION

Physical Parameters

Available Thickness	30µm (1.2mils) 40µm (1.5mils)
Unexposed Color in Yellow Light	Green
Exposed Color in Daylight	Blue
Exposed Color in Yellow Light	Dark Green
Print-Out (Phototropic) Image	Strong
Contrast to Copper	Strong
Odor	Low

SAFE HANDLING

Note safety and industrial hygiene precautions. Consult the Material Safety Data Sheet (MSDS) of any chemical used. MSDSs for Riston® dry film photoresists are available.

This data sheet documents specific process information for Riston® MM730 & MM740. For more background on general Riston® processing, see the General Processing Guide.

COPPER SURFACES AND SURFACE PREPARATION

Brush Pumice

3F or 4F grade, fused, 15-20% v/v, 9-12 mm (3/8-1/2") brush foot print, fines removal and replenishment per vendor recommendations; high-pressure (10 bar) final rinse (pH 6-8); hot air dry.

Jet Pumice

3F or 4F grade, unfused, 15-20% v/v, fines removal and replenishment per vendor recommendations; high-pressure (10 bar) (147 PSI) final rinse (pH 6-8); hot air dry.

Jet or Brush Aluminum Oxide (Al₂O₃)

Follow vendor recommendations.

Compressed Pad Brushing

500 grit; 7-9 mm (1/4-3/8") brush foot print; high-pressure (8-10 bar) final rinse (pH 6-8).

Bristle Brushing

500 grit; 7-9 mm (1/4-3/8") brush foot print; final rinse (2-3 bar), (pH 6-8).

Note: Electroplated copper surfaces for tent-and-etch applications are frequently "de-noduled" e.g. by compressed pad brushing prior to pumice scrubbing.

Control Tests

Water break test: 30 seconds

Ra: 0.10-0.3 µm Rz: 2-3 µm

To remove antitarnish conversion coatings (e.g. chromate conversion coatings) and/or copper tarnish (oxides), it is recommended to precede pumice or aluminum oxide scrubbing with a spray acid cleaner or 10-15% sulfuric acid or a microetch.

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Chemically Cleaned Copper

Use Alkaline Spray Cleaner (e.g. VersaCLEAN® 415) for removal of organic contaminants followed by a spray microetchant (e.g. SureETCH® 550) for conversion coating (chromate) and/or copper oxide removal (about 2-2.5 µm; 80-100 microinch etch). A 10% sulfuric acid spray may be used between alkaline cleaner and microetchant to help with the conversion coating removal. In this case, only 1.5 µm (60 microinch) microetch depth is required. To remove residual salts after microetching from the copper surface, an acid rinse or efficient water spray rinsing have been employed successfully. In-line systems for prelamination cleaning may not require an antitarnish treatment after chemical preclean to preserve the cleaned surface. Non-in-line systems with hold times of several hours will require antitarnish. For antitarnish selection: See “Electroless Copper with Antitarnish”.

Electrochemically Cleaned Copper

Conveyorized systems combining reverse current electrochemical cleaning and microetching are offered to effectively remove chromate conversion coatings with minimal copper removal. The alkaline electrochemical cleaner first removes trace organics and chromates. After a rinse, a microetch removes about 0.8µm (30 microinches) of copper. Following a second rinse, an antitarnish may be applied.

Double-Treated Copper Surfaces

Normally no prelamination cleaning required; vapor degreasing or chemical cleaning to remove organics is optional. Tacky roller cleaning recommended to remove particles.

LAMINATION

Lamination Conditions DuPont HRL-24

Pre-Heat	Optional
Roll Temperature	105 °C ±5°C (221 ±9°F)
Roll Speed	0.6-1.5 m/min (2-5 ft/min)
Air Assist Pressure	0-2.8 bar (0-40 psig)

Note: For 1.4 bar use heavy-duty rolls

Post-Lamination Hold Time

- Panels may be exposed immediately after lamination; however, allow enough time for panels to cool to room temperature before lamination (about 15 minutes; use accumulator in in-line systems)
- Minimize hold time (guidelines): 30 mins ~ 1 hr
- Maximum hold time (guidelines):
Lamination: Up to 2 days. Hold times should be determined empirically based on the temperature and relative humidity of the storage area

Note: Guideline—strip within 5 days after lamination.

Laminator Conditions DuPont ASL-24

Seal Bar Temp.	60 ± 10°C (140 ± 18°F)
Lam. Roll Pressure	3.0-5.0 bar (43-72 psig)
Lamination Temp.	105 ±5°C (220 ± 9°F)
Seal Time	1-4 seconds
Seal Bar Pressure	3.5-4.5 bar (50-65 psig)
Lamination Speed	1.5-3 m/min (5-10 ft/min)

Note: Reduced lamination roll pressure and/or temperature may be required in tenting applications to avoid tent breakage and resist flow into through-holes.

Panel Handling/Racking/ Stacking

Preferred: Vertical racking in slotted racks

Less desirable: Stacking

To minimize adverse effects: Stack on edge vertically after cooling; avoid dust and dirt trapping between panels; insert unlaminated panel between stack support and first laminated panel to protect laminated panel. Unlaminated support panel should be at least as big as the laminated panels. Thin flexible innerlayers usually cannot be racked. Preferred techniques: Hanging panels vertically or stacking on edge after cool down. If innerlayers are stacked horizontally in trays, the stack height should be limited especially for panels with thin photoresist and fine circuitry.

PERFORMANCE ON FLEXIBLE SUBSTRATES

MM700 can be used successfully on thin core laminate and flexible substrates.

EXPOSURE

Resolution (Lines & Spaces)

- In Optimized Production Environment by LDI with good development and rinse control: 30 micron (1.25mil) L/S for 30 µm resist
- In Lab Environment: 25 micron (1.0 mil L/S) for 30 µm resist

Exposure Energy vs “Steps Held” For Recommended Exposure Range

Riston® MM700	MM730	MM740
mJ/cm ²	12-22	14-26
RST	6-12	6-12
SST	5-8	5-8

- Steps held can vary by +/-1 RST depending on the development breakpoint used
- Energy is set by Orbotech Paragon LDI machine

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DEVELOPMENT

Chemistries/Make-up

Sodium carbonate, anhydrous, (soda ash), Na_2CO_3

- Working solution: 0.85 wt%. Use 8.5 g/l (0.071 lb./gal), e.g. for a 100 gallon sump use 7.1 lb

Sodium carbonate, monohydrate; $\text{Na}_2\text{CO}_3 \cdot \text{H}_2\text{O}$

- Working solution: 1.00 wt%. Use 10 g/l (0.083 lb./gal; e.g. for a 100 gallon sump use 8.3 lb.)

Potassium carbonate (potash; K_2CO_3)

- For make up, use either potassium carbonate powder, i.e. anhydrous (potash) K_2CO_3 or a liquid concentrate such as DuPont D-4000 developer (40% concentrate)
- Working solution: 1.0 wt%. For 100 liter solution, use 1.5 liter of D-4000 or 3.23 Kg of anhydrous potassium carbonate. For 100 gal solution, use 1.5 gal of D-4000 or 7.1 lb. of anhydrous potassium carbonate

Equations to calculate required amounts for desired wt% of working solutions

Na_2CO_3 : $\text{kg Na}_2\text{CO}_3 = \text{wt\%} \times \text{sump vol liters} \times 0.01\text{lb.}$ $\text{Na}_2\text{CO}_3 = \text{wt\%} \times \text{sump vol gallons} \times 0.083$

D-4000: liters (or gallons) D-4000 = wt% x sump vol liters (or gallons x 0.018)

K_2CO_3 : $\text{kg K}_2\text{CO}_3 = \text{wt\%} \times \text{sump vol liters} \times 0.01 \text{ lb.}$ $\text{K}_2\text{CO}_3 = \text{wt\%} \times \text{sump vol gallons} \times 0.083$

Control Test

Titration of fresh developer solution (e.g. 25ml), before defoamer addition, with 0.1 N HCl to the Methyl Orange end point.

$$\text{wt\%} = \text{N} \times \text{ml HCl} \times \text{FW} \times \text{ml Sample}$$

(N= acid normality; FW = formula weight)

$$\text{FW of Na}_2\text{CO}_3 = 106$$

$$\text{FW of Na}_2\text{CO}_3 \cdot \text{H}_2\text{O} = 124$$

$$\text{FW of K}_2\text{CO}_3 = 138$$

Defoamers

Riston® MM700 has been successfully used without defoamer. The need for defoamer and the amount required are dependent on water quality, carbonate purity, photoresist loading, and equipment design. If required, add 0.80 ml/liter (3 ml/gallon) of FoamFREE™ 940, or equivalent polyethylene-polypropylene glycol block co-polymer.

- For batch operation: Add defoamer during initial make up. For automatic replenishment systems: Add defoamer directly to the sump in a high turbulence area at a predetermined rate

Do not add defoamer to the supply tank or to the replenishment solution.

Development Conditions

- Spray Pressure: 1.4 –2.1 bar (20-30psig)
- Spray Nozzles: High impact direct-fan nozzles preferred; a combination of cone and fan nozzles may be preferred if film tent breakage is experienced
- Chemistry:
 - Na_2CO_3 : 0.7-1.2 wt%; 0.85 wt% preferred
 - $\text{Na}_2\text{CO}_3 \cdot \text{H}_2\text{O}$: 0.8-1.3 wt%; 1.0 wt% preferred
 - K_2CO_3 : 0.8-1.2 wt%; 1.0 wt% preferred
- Temperature: 27-35°C (80-95°F); 30°C (85°F) preferred
- Dwell Time
 - Breakpoint: 40-60%
 - Time in Developer (Dwell Time), at 1.4 bar (20 psig) spray pressure, 50% breakpoint. 30°C, fresh developer solution at recommended carbonate concentrations
 - Riston® MM730: 40 seconds
 - Riston® MM740: 50 seconds

Note: Total time in developer = Time to clean divided by breakpoint

- Time to clean (time in developer to wash off unexposed resist): 20 Seconds for Riston® MM730 (might vary by different conditions)
- Shorter times to clean are achieved at higher temperatures, higher carbonate concentrations, and higher pressures
- If developer conveyor speed is too fast for match with other in-line equipment: Lower soda ash concentration down as far as 0.5wt%; consider lowering temperature. Do not lower spray pressure below recommended levels

Resist Loading

Resist loading: 0-0.4 mil-m²/l(0-12 mil-ft²/gal)

Note: This range gives a fairly constant time to clean; lower loadings result in shorter time to clean; higher loadings increase the time to clean.

Rinsing & Drying Recommendations

- Rinse water: Hard water (150-250 ppm CaCO_3 equivalent). Softer water can be hardened by the addition of calcium chloride or magnesium sulfate. If hard water is not available, a first soft water rinse may be followed by a dilute acid rinse, followed by a water rinse
- Rinse temperature: 15-25°C (60-80°F)
- Rinse spray pressure: 1.4-2.1 bar (20-30 psig). Use high impact, direct-fan nozzles

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- Effective rinse length: 1/3-1/2 of length of developer chamber; >1/2 preferred
- Drying: Blow dry thoroughly; hot air preferred

Controls

- For batch processing: Adjust conveyor speed to maintain desired breakpoint; dump developer solution when development time has become 50% longer than for fresh solution
- Developer conveyor speed: See “Dwell Time”
- Feed & bleed: To keep loading at about 0.2 mil-m²/l (8 mil-ft²/gal), activate addition of fresh developer at pH 10.5; stop addition when pH 10.7 is reached

Hold Time after Development before Etching 0-5 Days

Note: Minimize white light exposure during post development hold to prevent film embrittlement.

Developer Maintenance

Clean at least once a week to remove resist residue, calcium carbonate (scale), defoamer, and dye from developed resist. Dye build-up can be minimized by the use of anti-foam.

ETCHING

Riston® MM700 resists are compatible with most acid etchants, e.g. cupric chloride (free HCl normality < 3.0 N), H₂O₂/H₂SO₄, and ferric chloride.

STRIPPING

Aqueous Caustic (NaOH or KOH) Conveyorized Stripping

Stripper Dwell Times (seconds) at 55°C (130°F), 1.7 kg/cm² (25psig), over recommended exposure range:

	MM730	MM740
3 wt% NaOH	33 ~ 38 sec	50 ~ 60 sec

Notes:

- Dwell Time = 2x Time to strip resist
- High caustic concentrations produce larger skin sizes and higher loading capabilities
- KOH generally produces smaller skin sizes than NaOH

Particle Size at 3.0% NaOH: Sheet

- Solubility of stripped particles: Non-soluble
- Physical characteristics of stripped particles (e.g. stickiness): Non-sticky
- Higher stripping temperature increases the stripping rate

- Stripping rate can be increased with higher impact sprays. Use higher pressures and/or high-impact spray nozzles. Avoid low impact deflector nozzles
- Time to strip increases with white light exposure. A 20% increase in strip time over 8 days exposure is not unusual
- Higher levels of exposure increase time-to-strip: Slightly

Defoamers

Additives for foam control may not be required depending on equipment design and operation. However, if defoamer is needed, use DuPont™ FoamFREE™ 940 at 0.8 ml/liter (3 ml/gallon) for resist loadings up to 0.6 mil-m²/liter (25 mil-ft²/gal).

Controls/Solution Maintenance

- Preferred: Continuous replenishment (feed & bleed) using board count. Maintain resist loading at <0.4 mil-m²/liter (<15 mil-square feet/ gallon)
- Batch: Up to 0.5 mil-m²/liter (20 mil-square feet/gallon). Maintain breakpoint at <50% by lowering conveyor speed or by starting batch stripping with a lower breakpoint and changing the solution once breakpoint moves above 50%. However, low breakpoints can lead to attack of solder on plated work, or cause copper oxidation
- Filtration systems spray stripping equipment should contain a filtration system to collect and remove resist skins to avoid nozzle clogging, to extend stripper life, and to avoid resist skins from reaching the rinse chamber. The most effective filter systems collect the stripper skins immediately after they were generated, before entering recirculation pumps, and they feature continuous removal of skins from the stripper solution

Equipment Cleaning

Cleaning of equipment: Drain and flush with water. Fill unit with 5 wt% KOH or NaOH, heat to 55°C (130°F), and circulate (spray) for 30 minutes to dissolve photoresist particles. Then drain the unit. Repeat procedure if required to remove heavy residues. Remaining blue dye stains on equipment may be removed by circulating 5 vol.% HCl at 55°C (130°F) for 30 minutes (HCl can damage stainless steel). Then drain the unit, fill with water, recirculate for 30 minutes, and drain. There are also proprietary cleaners available which may offer better results.

Proprietary Strippers

Used for higher strip speed, higher resist loading, to minimize chemical attack on tin or tin/lead, or to reduce copper oxidation, e.g. to facilitate AOI.



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Reworking Panels for Re-Use

Stripped panels may contain organic residues from photoresist or defoamers. After stripping, regenerate a fresh copper surface as follows, before mechanically cleaning the panels:

- Soak for three minutes in a hot soak cleaner at the recommended temperature
- Rinse thoroughly
- Etch 0.13 μm (5 microinches) of copper if panels are deeply oxidized
- Rinse thoroughly
- Dip in 5-10% sulfuric acid
- Rinse thoroughly
- Dry

SAFE LIGHTING

Protect photoresist through lamination and development steps from UV radiation and visible light up to 450 nm by use of yellow, amber or gold fluorescent "safe lights".

High intensity (<70 footcandles) yellow "safe light" causes a change in steps held and should be avoided.

WASTE DISPOSAL

For questions concerning disposal of photoresist waste, refer to the latest DuPont literature and Federal, State, and Local Regulations.

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